



Attachment - Replacement Abstract

Abstract of the Disclosure

A semiconductor device, including a gate electrode or dummy gate on a fin silicon layer, an impurity introduced into the fin silicon layer with the gate electrode or dummy gate used as mask so as to form first impurity regions, the gate electrode or dummy gate etched so as to form a gate electrode or dummy gate having a reduced size, and an impurity introduced into the fin silicon layer with the gate electrode or dummy gate of the reduced size used as a mask so as to form second impurity regions positioned adjacent to the first impurity diffusion regions.